

Notice of References Cited	Application/Control No. 09/905,398	Applicant(s)/Patent Under Reexamination LAYADI ET AL.
	Examiner Anh D. Mai	Art Unit 2814

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5231306	07-1993	Meikle et al.	257/751
	B	US-6069072	05-2000	Konecni et al.	438/642
	C	US-6221072	04-2001	Brennan	438/648
	D	US-			
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	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	JP-08-107148	04-1996	Japan	Yamashita et al.	H01L 21/768
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NON-PATENT DOCUMENTS

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	U	R. Wenzel et al., Diffusion Barriers on Titanium-Based Ohmic Contact Structures on SiC. IEEE 1998, pp. 159-164.
	V	K. Hieda et al., Low Temperature (Ba,Sr)TiO ₃ Capacitor Process Integration (LTB) Technology for Gigabit Scaled DRAMs. IEDM 1999, pp. 789-792.
	W	
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.